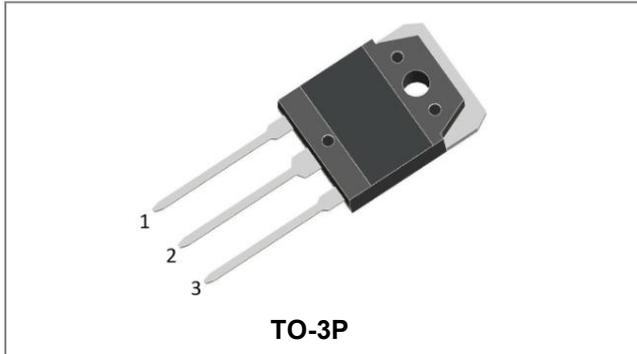


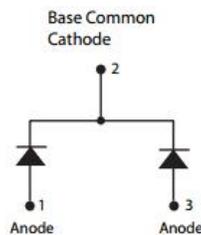
SDUR3060PT ULTRAFAST RECTIFIER



Applications:

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram



Features:

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- This is a Pb – free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	600	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_c=110^\circ\text{C}$, rectangular wave form	15(Per Leg) 30(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I_{FSM}	8.3ms, Half Sine pulse	150	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (Per Leg)*	V_{F1}	@ 15A, Pulse, $T_J = 25^\circ\text{C}$	1.3	1.8	V
	V_{F2}	@ 15A, Pulse, $T_J = 125^\circ\text{C}$	1.1	-	V
Reverse Current (Per Leg)*	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25^\circ\text{C}$	-	10	μA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125^\circ\text{C}$	-	250	μA
Reverse Recovery Time(Per Leg)	t_{rr}	$I_F=500\text{mA}, I_R=1\text{A}, \text{ and } I_{rm}=250\text{mA}$	50	60	ns

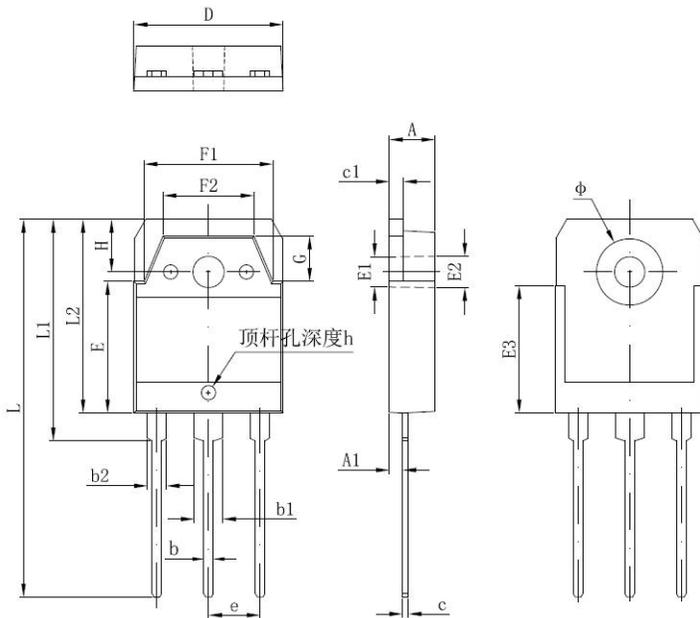
* Pulse width < 300 μs , duty cycle < 2%

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Thermal-Mechanical Specifications:

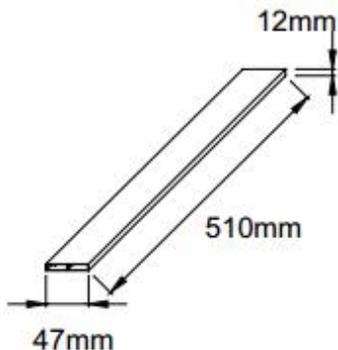
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T _J	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation	1.1	°C/W
Approximate Weight	wt	-	6.0	g
Case Style	TO-3P			

Mechanical Dimensions TO-3P

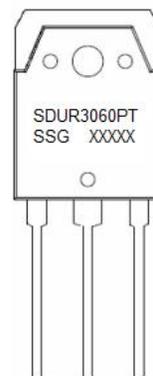


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.800	5.000	0.181	0.197
A1	1.200	1.600	0.047	0.063
b	0.800	1.200	0.031	0.047
b1	2.800	3.200	0.110	0.128
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.450	1.650	0.057	0.065
D	15.450	15.850	0.608	0.624
E	13.700	14.100	0.539	0.555
E1	3.200 REF		0.126 REF	
E2	3.300 REF		0.130 REF	
E3	13.450 REF		0.530 REF	
F1	13.400	13.800	0.528	0.543
F2	9.400	9.800	0.370	0.388
L	39.900	40.300	1.571	1.587
L1	23.200	23.600	0.913	0.929
L2	20.300	20.600	0.799	0.811
φ	6.900	7.100	0.272	0.280
G	5.150	5.550	0.203	0.219
e	5.450 TYP		0.215 TYP	
H	5.000 REF		0.197 REF	
h	0.000	0.300	0.000	0.012

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

- SDUR = Device Type
- 30 = Forward Current (30A)
- 60 = Reverse Voltage (600V)
- PT = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0



Ordering Information:

Device	Package	Shipping
SDUR3060PT	TO-3P(Pb-Free)	30pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

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